

Session Chairs

Monday, November 12, 2018

PL1: Plenary	9:00-11:30	Hiroshi Fujioka	Bernard Gil
ED1: Power Devices I	13:30-15:20	Jun Suda	Tetsu Kachi
CR1: Fluctuation & Localization	13:30-15:25	Nicolas Grandjean	Robert Martin
GR1: Doping	13:30-15:25	W. Alan Doolittle	Yoshihiro Kangawa
OD1: Tunnel Junction	13:30-15:25	Jung Han	Tim Wernicke
CR2: Structural Analysis	13:30-15:20	Catherine Bougerol	Shigetaka Tomiya
J1 (GR/OD): Nanostructures I	13:30-15:25	Fabien Massabuau	Satoshi Kamiyama
J2 (GR/ED): Growth for ED	17:25-19:00	Andrew Allermann	Koh Matsumoto
CR3: InGaN-based QWs I	17:25-18:50	Peter Parbrook	Ulrich T. Schwarz
GR2: AlGaIn I	17:25-18:55	Markus Weyers	Muhammad Ajmal Khan
ED2: Mg Implantation	17:25-18:55	Isik Kizilyalli	Siddharth Rajan
CR4: Red & Infrared Materials	17:25-18:55	Bo Shen	Yasushi Nanishi
J3 (GR/OD): Nanostructures II	17:25-18:55	Zetian Mi	Akihiko Kikuchi

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GR3: HVPE I	8:30-10:20	Jianfeng Wang	Narihito Okada
CR5: Defect Characterization I	8:30-10:25	Frank Bertram	Carol Trager-Cowan
OD2: Micro LED	8:30-10:25	Michael Krames	Seong-Ju Park
ED3: MOS	8:30-10:25	Tat-Sing Paul Chow	Heiji Watanabe
CR6: Carrier & Phonon Dynamics	8:30-10:25	Bo Monemar	Shigefusa Chichibu
OD3: Photodetectors	8:30-10:25	Chih-Chung Yang	Masatomo Sumiya
GR4: Liquid Growth	10:55-12:45	Tadao Hashimoto	Izabella Grzegory
CR7: Defect Characterization II	10:55-12:50	Christian Wetzel	Yoshihiro Ishitani
OD4: Device Physics	10:55-12:50	Jen-Inn Chyi	Hideki Hirayama
ED4: RF Devices	10:55-12:45	Tomás Palacios	Eiji Yagyu
J4 (GR/CR): InAlN & InAlGaIn	10:55-12:50	Jean-Francois Carlin	Takashi Matsuoka
OD5: InGaIn LED I	10:55-12:45	Junko Kobayashi	Atsushi A. Yamaguchi
GR5: AlGaIn II	14:50-16:40	Mitsuru Funato	Julien Brault
CR8: Impurities	14:50-16:45	Akihiko Yoshikawa	Axel Hoffmann
OD6: InGaIn LED II	14:50-16:40	Jong-In Shim	Lars Samuelson
ED5: Process I	14:50-16:35	Matteo Meneghini	Shinya Takashima
CR9: Theory & Simulation	14:50-16:35	Yuh-Renn Wu	Toru Akiyama
OD7: Novel Optical Devices I	14:50-16:45	Chia-Yen Huang	Hiroto Sekiguchi

Wednesday, November 14, 2018

OD8: VCSEL	8:00-9:25	Tien-Chang Lu	Piotr Perlin
J5 (GR/OD): Growth for OD I	8:00-9:30	Kazuhiro Ohkawa	Masakazu Sugiyama
CR10: Defect Characterization III	8:00-9:25	Detlef Hommel	Akira Sakai
ED6: Current Transport in Electron Devices	8:00-9:25	Kevin Chen	Takashi Egawa
GR6: MBE	8:00-9:30	Czeslaw Skierbiszewski	Tsutomu Araki
ED7: Sensors	8:15-9:30	Hutomo Suryo Wasisto	Taketomo Sato
OD9: InGaIn LD	10:00-11:25	Raphaël Butté	Tatsushi Hamaguchi
GR7: AlN I	10:00-11:30	Priti Gupta	Zlatko Sitar
CR11: Electrical Properties I	10:00-11:30	Jaime Freitas	Daigo Kikuta
ED8: Integrated Circuits	10:00-11:25	Patrick Fay	Kazuo Tsutsui
GR8: Epitaxial Growth I	10:00-11:30	Atsushi Nishikawa	Takayuki Nakano
ED9: Thermal Issues	10:00-11:00	Martin Kuball	Naoki Hara

Thursday, November 15, 2018

CR12: AlGa_N-based Materials	8:30-10:25	Michael Kneissl	Asif Khan
GR9: HVPE II	8:30-10:25	Ke Xu	Hajime Fujikura
OD10: Advanced Photonics	8:30-10:20	Euijoon Yoon	Bernard Gil
ED10: Nanowire Devices	8:30-10:25	Tamotsu Hashizume	Junichi Motohisa
GR10: Epitaxial Growth II	8:30-10:30	Bruno Daudin	Hisashi Murakami
OD 11: Device Process	8:30-10:15	Shyh Chiang Shen	Hong Tang
CR13: Single Photon Emission	10:55-12:45	Juergen Christen	Yasuhiko Arakawa
GR11: AIN II	10:55-12:55	Matthias Bickermann	Yoshinao Kumagai
OD12: InGa_N LED III	10:55-12:50	Aurelien David	Masafumi Jo
ED 11: Reliability	10:55-12:50	Georges Pavlidis	Kenji Shiojima
GR12: Growth for HEMTs	10:55-12:55	Stacia Keller	Yoshio Honda
OD13: Novel Optical Devices II	10:55-12:40	Jong Kyu Kim	Susumu Noda
CR14: Nanophotonics	14:30-16:25	Andreas Waag	Katsumi Kishino
LN1: Late News I (ED)	14:30-16:25	Fernando Ponce	Yohei Otoki
OD14: DUV LED I	14:30-16:25	James S. Speck	Motoaki Iwaya
ED12: Process II	14:30-16:30	Elison Matioli	Masaaki Kuzuhara
GR13: Semipolar & Nonpolar	14:30-16:30	Markus Pristovsek	Tomoyuki Tanikawa
J6 (GR/CR): BN	14:30-16:15	Kazuhiko Hara	Takashi Taniguchi

Friday, November 16, 2018

OD15: DUV LED II	8:30-10:25	Ramon Collazo	Shugo Nitta
GR14: N-polar	8:30-10:10	Tomasz Sochacki	Tetsuya Akasaka
CR15: InGa_N-based QWs II	8:30-10:25	Andreas Hangleiter	Tadeusz Suski
ED13: HEMTs	8:30-10:30	Gaudenzio Meneghesso	Takuma Nanjo
J7 (GR/OD): Growth for OD II	8:30-10:30	Yasufumi Fujiwara	Yoshiki Saito
ED14: Novel Electron Devices	8:30-10:15	Maciej Sawicki	Ryuji Katayama
OD16: DUV LD	10:55-12:50	Leo J. Schowalter	Hideto Miyake
GR15: New Growth Technique	10:55-12:50	Michal Bockowski	Akira Usui
CR16: Electrical Properties II	10:55-12:50	Giovanni Alfieri	Tetsuo Narita
ED15: Power Devices II	10:55-12:45	Debbdeep Jena	Satoshi Nakazawa
GR16: InGa_N	10:55-12:55	Xinqiang Wang	Kentaro Onabe
LN2: Late News II	10:55-12:55	Mark Holmes	Kazunobu Kojima
PL2: Plenary	14:50-16:10	Yoichi Kawakami	